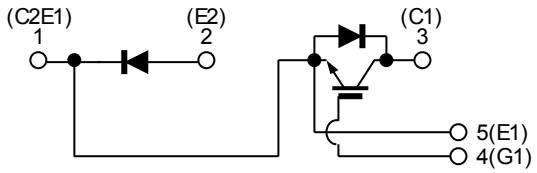
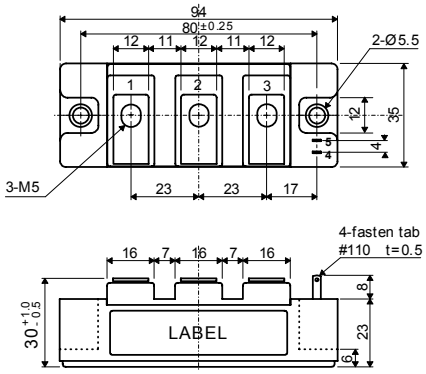
□



□



Dimension: mm

□

ollector- mitter oltage			
ate- mitter oltage		±	
ollector urrent			
ollector ower issipation			
unction emperature ange			
torage emperature ange			
(erminal to ase , inute) solation oltage		,	
ounting orque — odule ase to eatsink		.	(kgf cm)
ounting orque — usbar to ain erminal		.	(kgf cm)

□

			.	.	.	
ollector- mitter ut- ff urrent		= 1200V, = 0V			.	
ate- mitter eakage urrent		= ±20V, = 0V			.	μ
ollector- mitter aturation oltage		= 75A, = 15V		.	.	
ate- mitter hreshold oltage		= 5V, = 75mA	.		.	
nput apacitance		= 10V, = 0V, = 1MH		6,300		
witching ime — ise ime		= 600V = 8Ω = 13Ω = ±15V		.	.	μ
witching ime — urn-on ime				.	.	μ
witching ime — all ime				.	.	μ
witching ime — urn-off ime				.	.	μ

□

orward urrent			

			.	.	.	
eak orward oltage		= 75A, = 0V		.	.	
everse ecovery ime		= 75A, = -10V i/ t= 150A/μs		.	.	μ

□

				.	.	.	
hermal mpedance		th(j-c)	Junction to Case			.	
hermal mpedance	iode	th(j-c)	Junction to Case			.	

Fig.1- Output Characteristics (Typical)

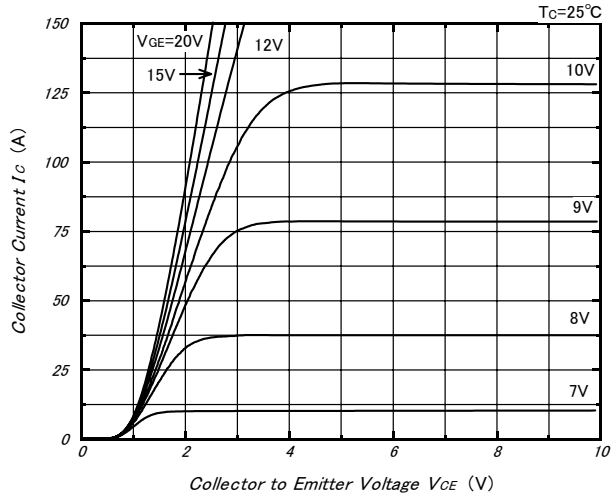


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

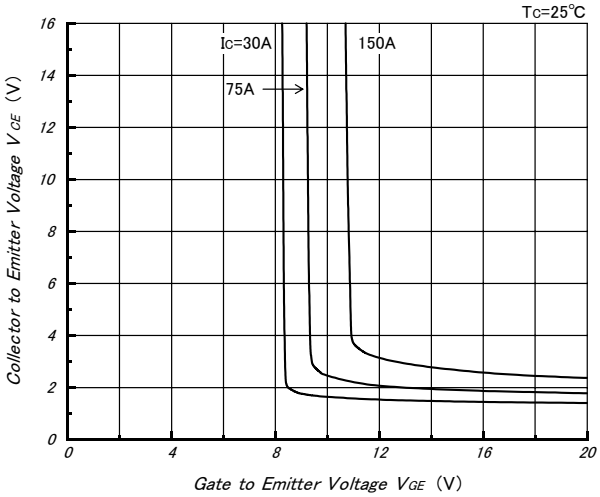


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

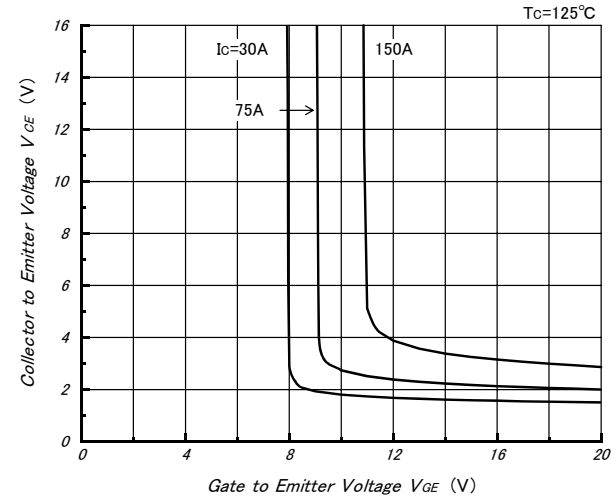


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

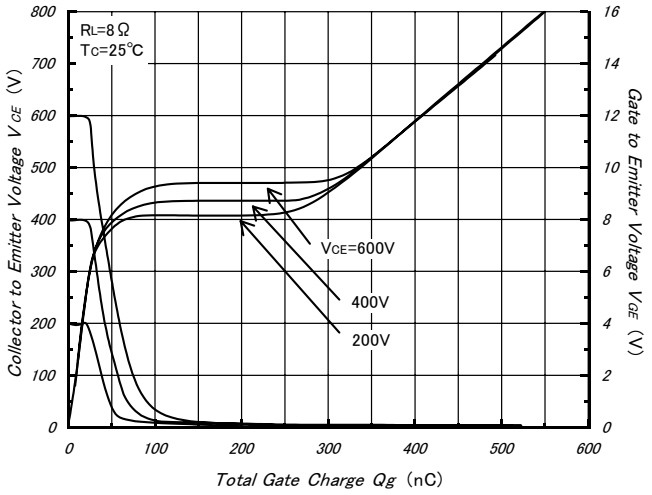


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

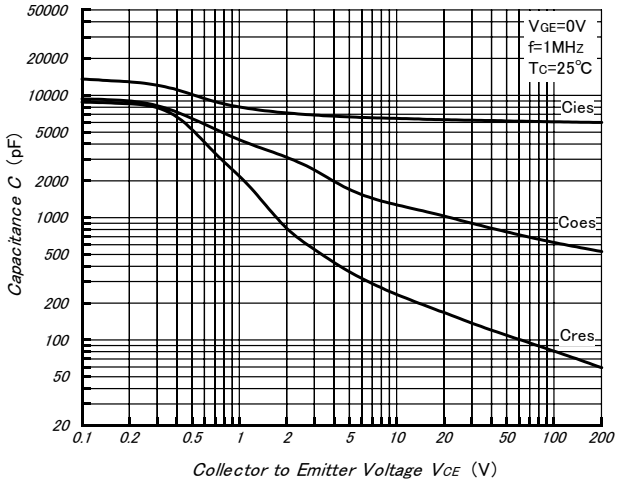


Fig.6- Collector Current vs. Switching Time (Typical)

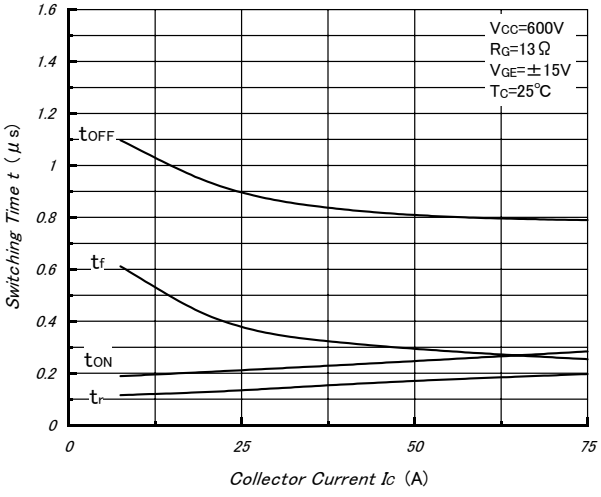


Fig.7- Series Gate Impedance vs. Switching Time (Typical)

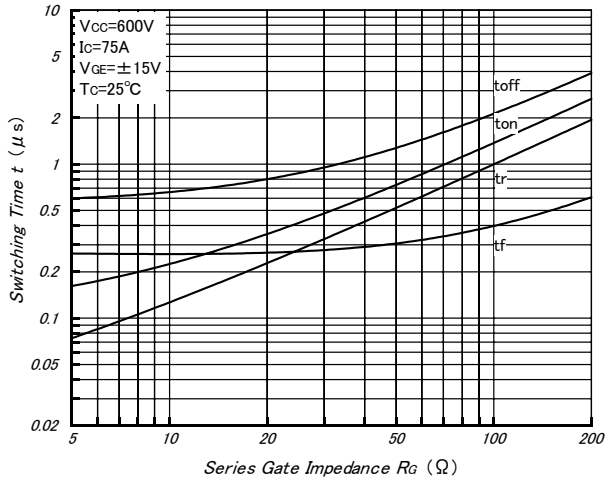


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

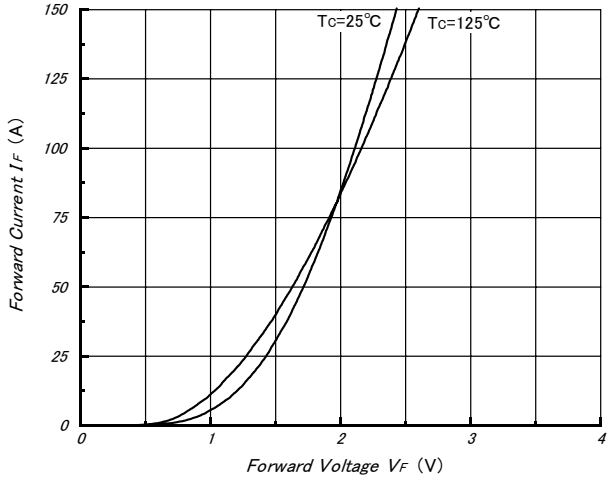


Fig.9- Reverse Recovery Characteristics (Typical)

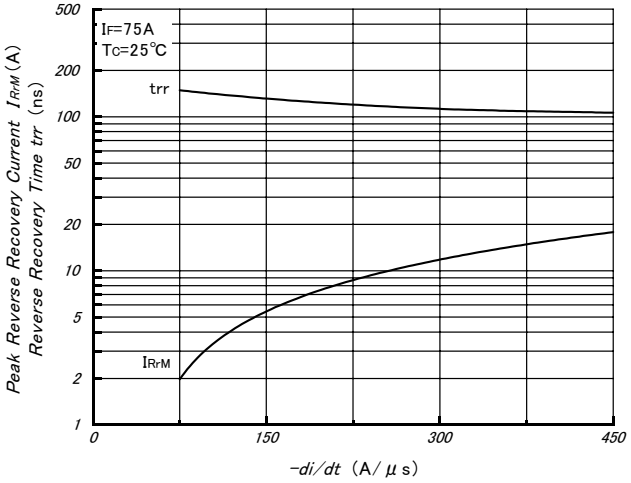


Fig.10- Reverse Bias Safe Operating Area

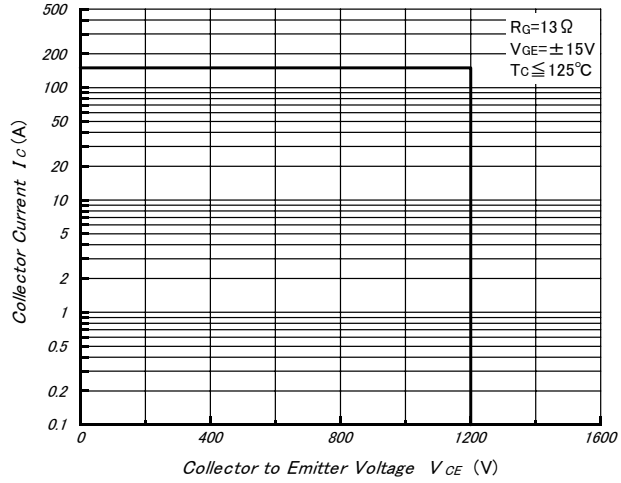


fig11-Tansient Thermal Impedance